

PBSS5360Z

60 V, 3 A PNP low VCEsat (BISS) transistor 19 February 2014

Product data sheet

General description 1.

PNP low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a medium power SOT223 (SC-73) Surface-Mounted Device (SMD) plastic package.

NPN complement: PBSS4360Z.

2. **Features and benefits**

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High energy efficiency due to less heat generation
- AEC-Q101 qualified

Applications

- DC-to-DC conversion
- Supply line switching
- Battery charger
- LCD backlighting
- Driver in low supply voltage applications (e.g. lamps and LEDs)
- Inductive load driver (e.g. relays, buzzers and motors)

Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|--------------------|---|---|-----|-----|-----|------|
| V _{CEO} | collector-emitter voltage | open base | - | - | -60 | V |
| I _C | collector current | | - | - | -3 | Α |
| I _{CM} | peak collector current | $t_p \le 1$ ms; single pulse | - | - | -6 | Α |
| R _{CEsat} | collector-emitter saturation resistance | I_C = -2 A; I_B = -200 mA; pulsed; $t_p \le 300$ μs; $\delta \le 0.02$; T_{amb} = 25 °C | - | - | 225 | mΩ |



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5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-------------|----------------------------|----------------|
| 1 | В | base | 4 | 2, 4 |
| 2 | С | collector | | 1— |
| 3 | Е | emitter | | . M |
| 4 | С | collector | ⊟1 ⊟2 ⊟3 SC-73 (SOT223) | 3 sym028 |

6. Ordering information

Table 3. Ordering information

| Type number | Package | | | | |
|-------------|---------|--|---------|--|--|
| | Name | Description | Version | | |
| PBSS5360Z | SC-73 | plastic surface-mounted package with increased heatsink; 4 leads | SOT223 | | |

7. Marking

Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
| PBSS5360Z | P5360Z |

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | | Min | Max | Unit |
|------------------|---------------------------|-------------------------------------|-----|-----|------|------|
| V_{CBO} | collector-base voltage | open emitter | | - | -80 | V |
| V _{CEO} | collector-emitter voltage | open base | | - | -60 | V |
| V _{EBO} | emitter-base voltage | open collector | | - | -7 | V |
| I _C | collector current | | | - | -3 | Α |
| I _{CM} | peak collector current | t _p ≤ 1 ms; single pulse | | - | -6 | Α |
| I _B | base current | | | - | -500 | mA |
| I _{BM} | peak base current | t _p ≤ 1 ms; single pulse | | - | -1 | Α |
| P _{tot} | total power dissipation | | [1] | - | 0.65 | W |
| | | | [2] | - | 1 | W |
| | | | [3] | - | 1.35 | W |

PBSS5360Z

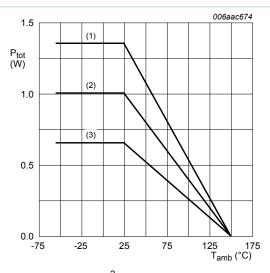
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| Symbol | Parameter | Conditions | | Min | Max | Unit |
|------------------|----------------------|------------|------------|-----|-----|------|
| | | | <u>[4]</u> | - | 2 | W |
| T _j | junction temperature | | | - | 150 | °C |
| T _{amb} | ambient temperature | | | -55 | 150 | °C |
| T _{stg} | storage temperature | | | -65 | 150 | °C |

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- [4] Device mounted on an FR4 PCB, 70 µm single-sided copper, tin-plated, mounting pad for collector 6 cm².



- (1) FR4 PCB, mounting pad for collector 6 cm²
- (2) FR4 PCB, mounting pad for collector 1 cm²
- (3) FR4 PCB, standard footprint

Fig. 1. Power derating curves

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9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|--|--|------------|-----|-----|-----|-----|------|
| R _{th(j-a)} thermal resistal from junction to ambient | thermal resistance | | [1] | - | - | 192 | K/W |
| | | | [2] | - | - | 125 | K/W |
| | ambient | | [3] | - | - | 93 | K/W |
| R _{th(j-sp)} | thermal resistance from junction to solder point | | | - | - | 16 | K/W |

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

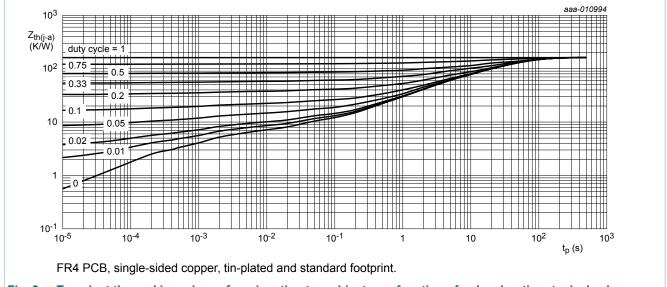
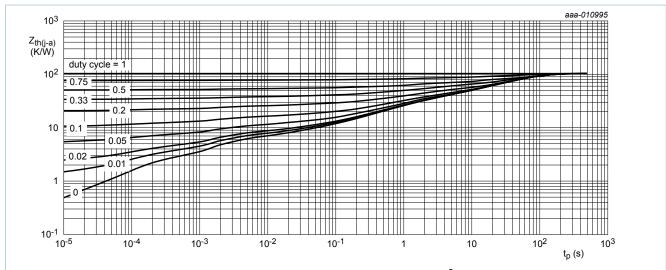


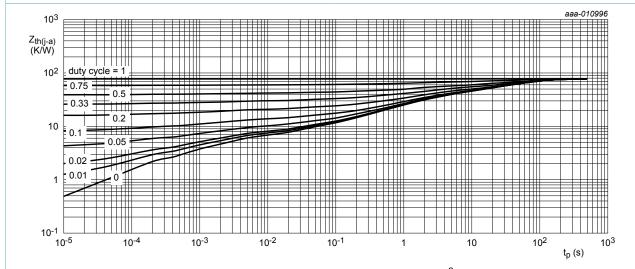
Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².

Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

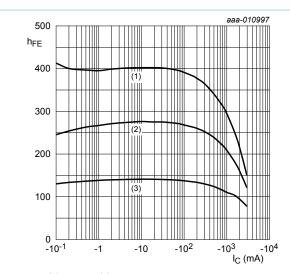
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10. Characteristics

Table 7. Characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit | |
|--------------------|---|---|---|-----|------|------|----|
| I _{CBO} | collector-base cut-off | V _{CB} = -48 V; I _E = 0 A; T _{amb} = 25 °C | - | - | -100 | nA | |
| | current | V_{CB} = -48 V; I_{E} = 0 A; T_{j} = 150 °C | - | - | -50 | μA | |
| I _{CES} | collector-emitter cut-off current | $V_{CE} = -48 \text{ V}; V_{BE} = 0 \text{ V}; T_{amb} = 25 \text{ °C}$ | - | - | -100 | nA | |
| I _{ЕВО} | emitter-base cut-off current | V_{EB} = -5 V; I_{C} = 0 A; T_{amb} = 25 °C | - | - | -100 | nA | |
| h _{FE} | DC current gain | V_{CE} = -5 V; I_{C} = -50 mA; T_{amb} = 25 °C | 150 | - | - | | |
| | | V_{CE} = -5 V; I_{C} = -500 mA; T_{amb} = 25 °C | 130 | - | - | | |
| | | V_{CE} = -5 V; I_{C} = -1 A; T_{amb} = 25 °C | 120 | - | - | | |
| | | V_{CE} = -5 V; I_{C} = -2 A; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C; pulsed | 100 | - | - | | |
| | | V_{CE} = -5 V; I_{C} = -3 A; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C; pulsed | 80 | - | - | | |
| V _{CEsat} | collector-emitter saturation voltage | I_{C} = -500 mA; I_{B} = -50 mA; T_{amb} = 25 °C | - | - | -150 | mV | |
| | | | I_C = -1 A; I_B = -100 mA; $t_p \le 300$ μs; $δ \le 0.02$; T_{amb} = 25 °C; pulsed | - | - | -200 | mV |
| | | I_{C} = -2 A; I_{B} = -200 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb}$ = 25 °C | - | - | -450 | mV | |
| | | I_{C} = -3 A; I_{B} = -300 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb}$ = 25 °C | - | - | -550 | mV | |
| R _{CEsat} | collector-emitter saturation resistance | $I_{\rm C}$ = -2 A; $I_{\rm B}$ = -200 mA; pulsed; $t_{\rm p} \le 300~\mu {\rm s}; \ \delta \le 0.02; \ T_{\rm amb}$ = 25 °C | - | - | 225 | mΩ | |
| V _{BEsat} | base-emitter saturation voltage | I_{C} = -1 A; I_{B} = -100 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb}$ = 25 °C | - | - | -1.2 | V | |
| V_{BEon} | base-emitter turn-on voltage | V_{CE} = -5 V; I_{C} = -1 A; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb}$ = 25 °C | - | - | -1.1 | V | |
| fτ | transition frequency | V_{CE} = -10 V; I_{C} = -50 mA; f = 100 MHz; T_{amb} = 25 °C | 65 | 130 | - | MH | |
| C _c | collector capacitance | V_{CB} = -10 V; I_{E} = 0 A; i_{e} = 0 A; f = 1 MHz; T_{amb} = 25 °C | - | 28 | 32 | pF | |

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$$V_{CE} = -5 V$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55$$
 °C

Fig. 5. DC current gain as a function of collector current; typical values

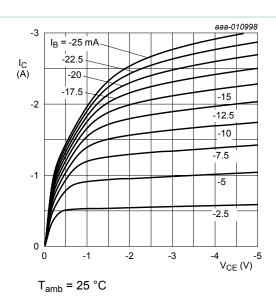
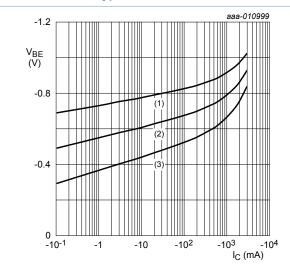


Fig. 6. Collector current as a function of collectoremitter voltage; typical values



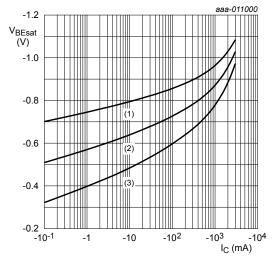
$$V_{CE} = -5 V$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 7. Base-emitter voltage as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 20$$

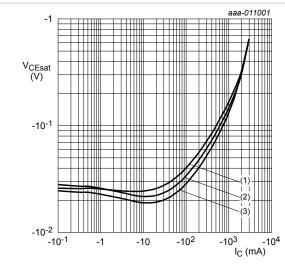
(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 8. Base-emitter saturation voltage as a function of collector current; typical values

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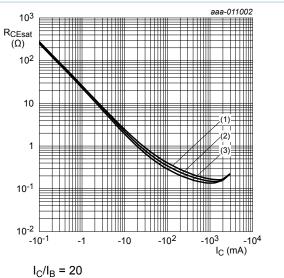
$$I_C/I_B = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values



(1)
$$T_{amb}$$
 = 100 °C

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values

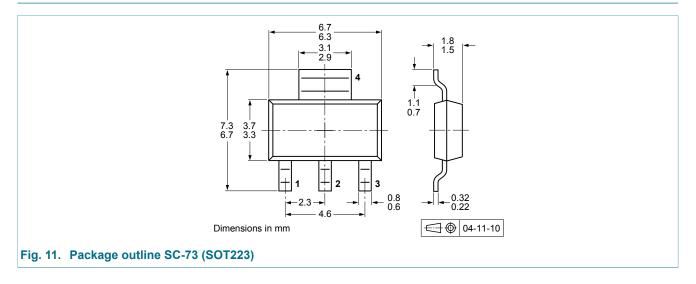
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11. Test information

11.1 Quality information

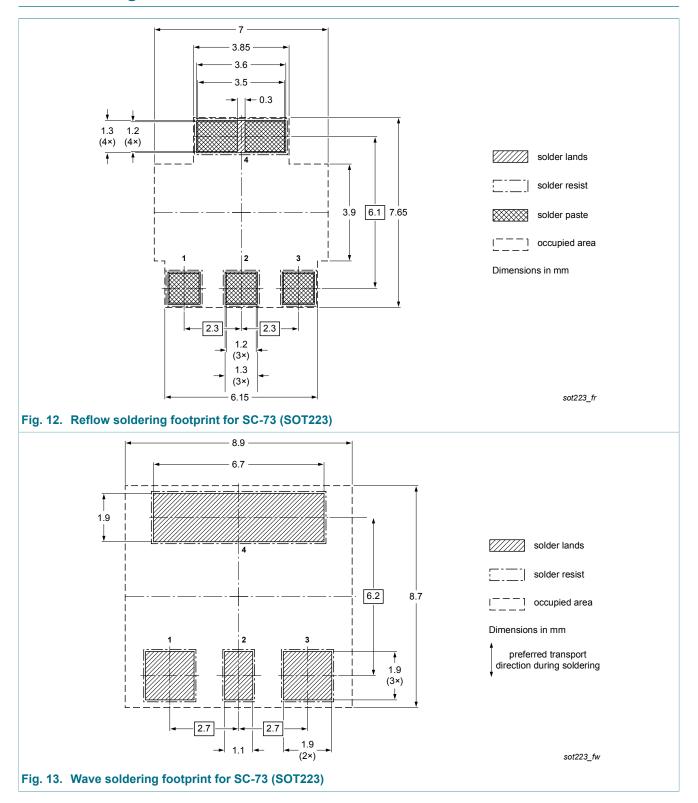
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

12. Package outline



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13. Soldering



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14. Revision history

Table 8. **Revision history**

| Data sheet ID | Release date | Data sheet status | Change notice | Supersedes |
|---------------|--------------|--------------------|---------------|------------|
| PBSS5360Z v.1 | 20140219 | Product data sheet | - | - |

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| Document status [1][2] | Product status [3] | Definition |
|--------------------------------------|--------------------|---|
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